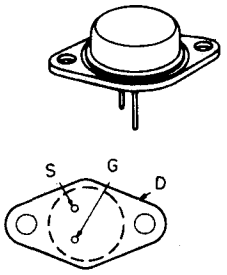



# Power MOSFETS

| ECG Type                           | Description and Application               | Transconductance gfs mhos | Drain to Source Breakdown Voltage BV <sub>DSS</sub> | Gate to Source Breakdown Voltage BV <sub>GS</sub> | Continuous Drain Current I <sub>D</sub> Amps | Gate to Source Threshold Voltage V <sub>GS</sub> (th) | Drain to Source Resistance r <sub>DS(on)</sub> Ohms | Input Cap C <sub>iss</sub> pf | Device Dissipation @T <sub>C</sub> =25°C PD Watts | Package   |
|------------------------------------|---|---------------------------|---|---|--|---|---|-------------------------------|---|---|
|                                    |   |                           |   |   |  |   |   |                               |   | Case/Fig./Basing  |
| ECG2392<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 6 Min                     | 100 Min   | ±20 Max*  | 32   | 4 Max   | .06 Max   | 1500 Typ                      | 125 Max   | TO-3<br>Fig. T28<br>   |
| ECG2386<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 2 Min                     | 600 Min   | ±20 Max*  | 6  | 4.5 Max   | 1.2 Max   | 1800 Max                      | 150 Max   |   |
| ECG2384<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 1.8 Min                   | 800 Min   | ±20 Max*  | 6  | 4 Max   | 1.5 Max   | 3500 Max                      | 125 Max   |   |
| ECG2390<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 3 Min                     | 60 Min  | ±20 Max*  | 12   | 4.5 Max   | .2 Max  | 800 Max                       | 75 Max  | TO-220<br>Fig. T41<br> |
| ECG2389<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 8 Min                     | 60 Min  | ±30 Max*  | 35   | 4 Max   | .045 Max  | 2000 Max                      | 125 Max   |   |
| ECG2395<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 17 Min                    | 60 Min  | ±30 Max*  | 50   | 4 Max   | .028 Max  | 2000 Max                      | 150 Max   |   |
| ECG2382<br>▲<br>(Compl to ECG2383) | MOSFET, N-Ch, Enhancement Hi Speed Switch | 1.5 Min                   | 100 Min   | ±20 Max*  | 8  | 4 Max   | .5 Max  | 750 Max                       | 75 Max  |   |
| ECG2383<br>▲<br>(Compl to ECG2382) | MOSFET, P-Ch, Enhancement Hi Speed Switch | 2 Min                     | 100 Min   | ±20 Max*  | 8  | 4.5 Max   | .4 Max  | 1200 Max                      | 75 Max  |   |
| ECG66<br>▲                         | MOSFET, N-Ch, Enhancement Hi Speed Switch | 3 Min                     | 100 Min   | ±20 Max*  | 12   | 4.5 Max   | .18 Max   | 1200 Max                      | 75 Max  |   |
| ECG2396<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 12 Min                    | 100 Min   | ±30 Max*  | 30   | 4 Max   | .057 Max  | 2000 Max                      | 150 Max   |   |
| ECG2388<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 5 Min                     | 200 Min   | ±20 Max*  | 12.5   | 4 Max   | .2 Max  | 1000 Typ                      | 75 Max  |   |
| ECG67<br>▲                         | MOSFET, N-Ch, Enhancement Hi Speed Switch | 2 Min                     | 400 Min   | ±20 Max*  | 5  | 4.5 Max   | 1.5 Max   | 1200 Max                      | 75 Max  |   |
| ECG2391<br>▲                       | MOSFET, N-Ch, Enhancement Hi Speed Switch | 2.1 Min                   | 400 Min   | ±30 Max*  | 4  | 4 Max   | 1.8 Max   | 500 Max                       | 75 Max  |   |

\* Warning - Exceeding BV<sub>GS</sub> maximum will result in permanent damage to the gate region oxide layer.  
 ▲ Refer to MOSFET Handling Precautions - Page 1-31

Package Outlines - See Page 1-78